ELECTRONICS, INC.
44 FARRAND STREET
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NTE1829
Integrated Circuit
Quad Transistor Array, 5kΩ

Features:
- 4 Circuits
- Output Current: I_C = 50mA
- Breakdown Voltage: V_{CEO} = 24V
- Built–In Base Current Limiting Resistor

Absolute Maximum Ratings: (T_A = +25°C unless otherwise specified)

Collector–Base Voltage, V_{CBO} 50V
Collector–Emitter Voltage, V_{CEO} 24V
Collector Substrate Voltage, V_{CIO} 50V
Collector Current, I_C 50mA
Input Voltage, V_1 . . . . . –0.5V to 50V
Collector Power Dissipation (Per Transistor), P_C 250mW
Power Dissipation, P_D 1000mW
Operating Ambient Temperature Range, T_{opr} . . . . . –30° to +75°C
Storage Temperatuere Range, T_{stg} . . . . . –55° to +150°C

Electrical Characteristics: (T_A = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector–Base Voltage	V_{CBO}	I_C = 10μA, I_E = 0	50	–	–	V
Collector–Emitter Voltage	V_{CEO}	I_C = 1mA, I_B = 0	24	–	–	V
Collector Leakage Current	I_{CEO}	V_{CE} = 10V, R_{BE} = ∞	–	–	1	μA
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = 5mA, I_I = 0.55mA	–	0.1	0.2	V
		I_C = 25mA, I_I = 2.25mA	–	0.3	0.4	V
Input Voltage	V_I	V_{CE} = 300mV, I_C = 5mA	–	1.2	2.2	V
		V_{CE} = 500mV, I_C = 25mA	–	3.0	5.1	V
Input Current	I_I	I_C = 5mA, V_1 = 5V	–	0.85	1.2	mA
		I_C = 25mA, V_1 = 15V	–	2.9	4.2	mA

Pin Connection Diagram
(Front View)



